



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

WBFBP-03D Plastic-Encapsulate DIODE

DK4448CLLD03 SWITCHING DIODE

DESCRIPTION

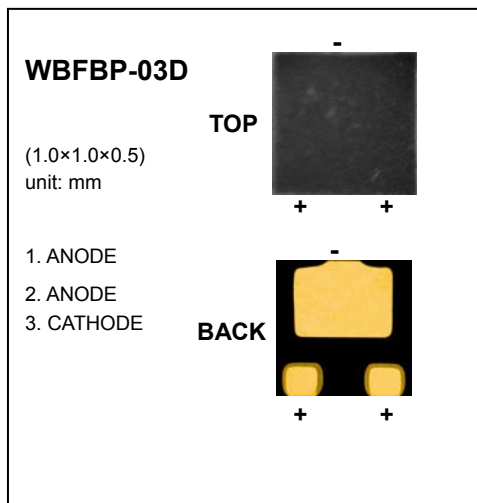
Epitaxial planar Silicon diode

FEATURES

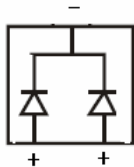
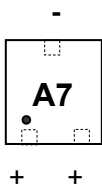
Fast Switching Speed
Ultra-Small Surface Mount Package
For General Purpose Switching Applications
High Conductance
Lead Free Product

APPLICATION

High Conductance Ultra Fast Diode
For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM,
DVD-ROM, Note book PC, etc.)



MARKING: A7



Maximum Ratings and Electrical Characteristics, Single Diode @T_A=25

Parameter	Symbol	Limits	Unit
Non-Repetitive Peak reverse voltage	V _{RM}	100	V
Peak Repetitive Peak reverse voltage	V _{RRM}	80	V
Working Peak Reverse Voltage	V _{RWM}		
DC Blocking Voltage	V _R		
RMS Reverse Voltage	V _{R(RMS)}	57	V
Forward Continuous Current	I _{FM}	500	mA
Average Rectified Output Current	I _O	250	mA
Peak forward surge current @=1.0μs @=1.0s	I _{FSM}	4.0 2.0	A
Power Dissipation	P _D	100	mW
Thermal Resistance Junction to Ambient	R _{θJA}	1250	°C/W
Storage temperature	T _{STG}	-65 to +150	°C

Electrical Ratings @T_A=25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	V _R	80			V	I _R =2.5μA
Forward voltage	V _{F1}	0.62		0.72	V	I _F =5mA
	V _{F2}			0.855	V	I _F =10mA
	V _{F3}			1.0	V	I _F =100mA
	V _{F4}			1.25	V	I _F =150mA
Reverse current	I _{R1}			0.1	μA	V _R =70V
	I _{R2}			25	nA	V _R =20V
Capacitance between terminals	C _T			3.5	pF	V _R =6V, f=1MHz
Reverse Recovery Time	t _{rr}			4	ns	V _R =6V, I _F =5mA

Typical Characteristics

DK4448CLLD03

